











TPS2421-1, TPS2421-2

SLUS907I - JANUARY 2009 - REVISED JANUARY 2015

# TPS242x 5-A, 20-V Integrated FET Hot Swap

#### **Features**

- Integrated Pass MOSFET
- Up to 20-V Bus Operation
- Programmable Fault Current
- Current Limit Proportionally Larger than Fault
- Programmable Fault Timer
- Internal MOSFET Power Limiting
- Latch-Off on Fault (TPS2421-1) and Retry (TPS2421-2) Versions
- SO-8 PowerPad™ Package
- -40°C to 125°C Junction Temperature Range
- UL2367 Recognized File Number E169910

# **Applications**

- **RAID Arrays**
- **Telecommunications**
- Plug-In Circuit Boards
- **Disk Drives**
- **SSDs**
- **PCIE**
- Fan Control

## 3 Description

The TPS2421 device provides highly integrated hot swap power management and superior protection in applications where the load is powered by busses up to 20 V. The TPS2421 device is well suited to standard bus voltages as low as 3.3 V because of the maximum-UV turn-on threshold of 2.9 V. These devices are very effective in systems where a voltage bus must be protected to prevent shorts from interrupting or damaging the unit. The TPS2421 device is an easy to use devices in an 8-pin PowerPad™ SO-8 package.

The TPS2421 device has multiple programmable protection features. Load protection is accomplished by a non-current limiting fault threshold, a hard current limit, and a fault timer. The current dual thresholds allow the system to draw short high current pulses, while the fault timer is running, without causing a voltage droop at the load. An example of this is a disk drive startup. This technique is ideal for loads that experience brief high demand, but benefit from protection levels in-line with their average current draw.

Hotswap MOSFET protection is provided by power limit circuitry which protects the internal MOSFET against SOA related failures.

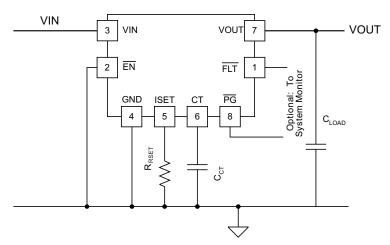
The TPS2421 device is available in latch-off on fault (TPS2421-1) and retry on fault (TPS2421-2).

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS2421-1	LICOD (0)	4 00
TPS2421-2	HSOP (8)	4.89mm x 3.90mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

# Typical Application





# **Table of Contents**

1	Features 1		9.3 Feature Description	12
2	Applications 1		9.4 Device Functional Modes	13
3	Description 1		9.5 Programming	16
4	Typical Application1	10	Application and Implementation	17
5	Revision History2		10.1 Application Information	17
6	Device Comparison Table 5		10.2 Typical Application	17
7	Pin Configuration and Functions 5	11	Power Supply Recommendations	20
8	_		11.1 PowerPad™	20
0	Specifications	12	Layout	21
	8.1 Absolute Maximum Ratings		12.1 Layout Guidelines	21
	8.2 ESD Ratings		12.2 Layout Example	21
	8.3 Recommended Operating Conditions	13	Device and Documentation Support	22
	8.4 Thermal Information		13.1 Related Links	
	8.5 Electrical Characteristics		13.2 Trademarks	22
_	8.6 Typical Characteristics		13.3 Electrostatic Discharge Caution	22
9	Detailed Description		13.4 Glossary	
	9.1 Overview	14	Mechanical, Packaging, and Orderable	
	9.2 Functional Block Diagram 11	• •	Information	22

# **5 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	changes from Revision H (January 2014) to Revision I	Page
•	Changed the package and ordering information to the Device Comparison Table	5
•	Added the I/O column to the Pin Functions table	5
•	Added the ESD Ratings table and changed the CDM value From: 400V To: ±500V	6
•	Replaced the Dissipation Ratings table with the <i>Thermal Information</i> table	6
•	Added the Detailed Description section	11
•	Changed the PIN DESCRIPTION section to the Feature Description section	12
•	Added the Application and Implementation section	17
•	Added the Power Supply Recommendations section	20
•	Added Figure 23	21

CI	nanges from Revision G (May 2013) to Revision H	Page
•	Deleted minimum voltage from voltage range in the document title, features list and description	1
•	Added 5-A to document title	1
•	Changed listed to recognized in UL FEATURES bullet, also added specific UL number	1
•	Added SSDs, PCIE, and Fan Control to the APPLICATIONS list	1
•	Added maximum-UV turn-on threshold of 2.9 V sentence to the first paragraph of the DESCRIPTION	1
•	Deleted capacitor, $C_{VIN}$ , and diode from the <i>Typical Application</i> image. Also changed $R_{SET}$ to $R_{RSET}$ and $C_{OUT}$ to $C_{LOAD}$ . Removed voltage range and changed OUT to VOUT. Also removed note on the former $C_{OUT}$ stating that this is only required in systems with lead and/or load inductance	
•	Changed C <sub>OUT</sub> to C <sub>LOAD</sub> and R <sub>SET</sub> to R <sub>RSET</sub> throughout document	1
•	Changed current limit value of the ISET description from 125% to 150% in the <i>Pin Functions</i> table. Also removed <i>TPS2421 only</i> text form this description	5
•	Changed C <sub>OUT</sub> to C <sub>VOUT</sub> for the power limit parameter in the <i>Electrical Characteristics</i> table	7
•	Changed $R_{SET}$ = 100 kW to $R_{RSET}$ = 100 k $\Omega$ in the FAULT CURRENT vs JUNCTION TEMPERATURE graph	9
•	Added note for TPS2421-1 to the VIN description in the PIN DESCRIPTION section	13

Submit Documentation Feedback

Copyright © 2009–2015, Texas Instruments Incorporated



•	Changed $V_{IN}$ to $V_{VIN}$ in the functional block diagram, Equation 6, and Equation 7	
<u>.</u>	Changed In to V <sub>VIN</sub> in Equation 21	18
Cł	nanges from Revision G (May 2013) to Revision H	Page
•	Deleted minimum voltage from voltage range in the document title, features list and description	1
•	Added 5-A to document title	1
•	Changed listed to recognized in UL FEATURES bullet, also added specific UL number	1
•	Added SSDs, PCIE, and Fan Control to the APPLICATIONS list	1
•	Added maximum-UV turn-on threshold of 2.9 V sentence to the first paragraph of the DESCRIPTION	1
•	Deleted capacitor, $C_{VIN}$ , and diode from the <i>Typical Application</i> image. Also changed $R_{SET}$ to $R_{RSET}$ and $C_{OUT}$ to $C_{LOAD}$ . Removed voltage range and changed OUT to VOUT. Also removed note on the former $C_{OUT}$ stating that this is only required in systems with lead and/or load inductance	
•	Changed C <sub>OUT</sub> to C <sub>LOAD</sub> and R <sub>SET</sub> to R <sub>RSET</sub> throughout document	1
•	Changed current limit value of the ISET description from 125% to 150% in the <i>Pin Functions</i> table. Also removed <i>TPS2421 only</i> text form this description	
•	Changed C <sub>OUT</sub> to C <sub>VOUT</sub> for the power limit parameter in the <i>Electrical Characteristics</i> table	<mark>7</mark>
•	Changed $R_{SET}$ = 100 kW to $R_{RSET}$ = 100 k $\Omega$ in the FAULT CURRENT vs JUNCTION TEMPERATURE graph	9
•	Added note for TPS2421-1 to the VIN description in the PIN DESCRIPTION section	13
•	Changed $V_{IN}$ to $V_{VIN}$ in the functional block diagram, Equation 6, and Equation 7	
•	Changed In to V <sub>VIN</sub> in Equation 21	18
<u>.</u>	nanges from Revision F (April 2013) to Revision G  Deleted I <sub>SET</sub> , C <sub>T</sub> Voltage from the <i>Absolute Maximum Ratings</i> <sup>(1)</sup> table	Page 6
Cł	nanges from Revision E (September 2011) to Revision F	Page
•	Changed C <sub>CT</sub> values From: MIN = 100 pF/μF To 0.1 nF and MAX From: 10 pF/μF To: in the <i>Recommended Operating Conditions</i> table	6
•	Added R <sub>RSET</sub> to the Recommended Operating Conditions table	6
•	Changed the conditions statement of the Electrical Characteristics table	<mark>7</mark>
•	Changed the TEST CONDITIONS for R <sub>ON</sub>	7
•	Changed I <sub>LIM</sub> / I <sub>FLT</sub> To: I <sub>LIM</sub> / I <sub>SET</sub>	7
•	Changed the conditions statement of the Electrical Characteristics table	8
•	Changed the PIN DESCRIPTION section	12
•	Changed the Application Information section.	17
CI	nanges from Revision D (August 2010) to Revision E	Page
_		
•	Changed SQUATION 2 from DISLET to DISSET and ISAULT to ISSET	
<u>.</u>	Changed equation 3 from RIFLT to RISET and IFAULT to ISET	12
Cł	nanges from Revision C (July 2010) to Revision D	Page
•	Added Feature: UL Listed - File Number E169910	1



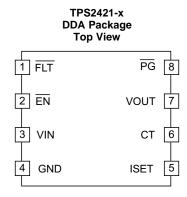
С	Changes from Revision B (June 2010) to Revision C	Page
•	Changed T <sub>SD</sub> (ms) column in Table 3. (the table was deleted in revision F)	15
С	Changes from Revision A (March 2009) to Revision B	Page
•	Added For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder on www.ti.com	



# 6 Device Comparison Table

DEVICE	FEATURE
TPS2421-1	Latchoff
TPS2421-2	Auto-retry

# 7 Pin Configuration and Functions



## **Pin Functions**

FUNCTION	FUNCTION PIN NO. I/O DESCRIPTION			
FLT	1	0	Fault low indicated the fault time has expired and the FET is switched off.	
EN	2	I	Device is enabled when this pin is pulled low	
VIN	3	I	ver In and control supply voltage	
GND	4	_	ND	
ISET	5	I/O	esistor to ground sets the fault current, the current limit is 150% of the fault current.	
СТ	6	I/O	capacitor to ground sets the fault time	
VOUT	7	0	utput to the load	
PG	8	0	Power Good low represents the output voltage is within 300 mV of the input voltage	



# 8 Specifications

# 8.1 Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted) (2)

	MIN	MAX	UNIT
Input voltage range, V <sub>VIN</sub> , V <sub>VOUT</sub>	-0.3	25	
Voltage range, FLT, PG	-0.3	20	V
Maximum continuous output current, I <sub>MAX</sub>		9	Α
Output sink current, FLT, PG		10	mA
Input voltage range, EN	-0.3	6	
Voltage range, CT, (3) ISET (3)	-0.3	3	V
Operating junction temperature range, T <sub>J</sub> Internally Limited		/ Limited	٥.
Storage temperature range, T <sub>stg</sub>	-65	150	ç

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 8.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2500	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±500	V

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 8.3 Recommended Operating Conditions

		MIN	NOM MA	λX	UNIT
$V_{VIN}, V_{VOUT}$	Input voltage range	3		20	
EN	Voltage range	0		5	V
FLT, PG	Voltage range	0		20	
I <sub>OUT</sub>	Continuous output current	0		6	Α
FLT, PG	Output sink current	0		1	mA
C <sub>CT</sub>		0.1			nF
R <sub>RSET</sub>		49.9	2	00	kΩ
T <sub>J</sub>	Junction temperature	-40	1	25	°C

## 8.4 Thermal Information

		TPS2421-x	
	THERMAL METRIC <sup>(1)</sup>	DDA	UNIT
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	41.3	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	44.7	
$R_{\theta JB}$	Junction-to-board thermal resistance	22.3	20044
Ψлт	Junction-to-top characterization parameter	5.3	°C/W
ΨЈВ	Junction-to-board characterization parameter	22.2	
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance	3.1	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

<sup>(2)</sup> All voltage values are with respect to GND.

<sup>(3)</sup> Do not apply voltage to these pins.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



## 8.5 Electrical Characteristics

Unless otherwise noted: 3 V  $\leq$  V<sub>VIN</sub>  $\leq$  18 V,  $\overline{EN}$  = 0 V,  $\overline{PG}$  =  $\overline{FLT}$  = open, R<sub>OUT</sub> = open, R<sub>RSET</sub> = 49.9 k $\Omega$ ,  $-40^{\circ}$ C  $\leq$  T<sub>J</sub>  $\leq$  125 $^{\circ}$ C, No external capacitor connected to VOUT

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
VIN							
	UVLO	VIN rising		2.6	2.85	2.9	V
		Hysteresis		150		mV	
	Bias current	<del>EN</del> = 2.4 V		25	100	μA	
		<u>EN</u> = 0 V			3.9	5	mA
VIN, V	OUT			•		,	
	R <sub>ON</sub>	$R_{VIN-VOUT}$ , $I_{VOUT} < I_{LIM}$ , 1 A $\leq I_{VOUT} \leq 4.5$ A			33	50	mΩ
	Power limit TPS242x	$V_{VIN}$ : 12 V, $C_{VOUT}$ = 1000 $\mu$ F, $\overline{EN}$ : 3 V $\rightarrow$ 0 V		3	5	7.5	
	Reverse diode voltage	$V_{VOUT} > V_{VIN}$ , $\overline{EN} = 5$ V, $I_{VIN} = -1$ A			0.77	1	V
ISET							
		$I_{VOUT} \uparrow$ , $I_{CT}$ : sinking $\rightarrow$ sourcing, pulsed test					
			$R_{RSET} = 200 \text{ k}\Omega$	0.8		1.2	
		0°C ≤ T <sub>J</sub> ≤ 85°C	$R_{RSET} = 100 \text{ k}\Omega$	1.8		2.2	
$I_{SET}$	Fault current threshold		$R_{RSET} = 49.9 \text{ k}\Omega$	3.6		4.4	Α
	anoonoid	-40°C ≤ T <sub>J</sub> ≤ 125°C	$R_{RSET} = 200 \text{ k}\Omega$	0.75		1.25	
			$R_{RSET} = 100 \text{ k}\Omega$	1.75		2.25	
			$R_{RSET} = 49.9 \text{ k}\Omega$	3.6		4.4	
		$R_{RSET} = 200 \text{ k}\Omega$	·	1.1	1.8	2.6	
I <sub>LIM</sub> / I <sub>SET</sub>	Ratio I <sub>LIM</sub> / I <sub>SET</sub>	$R_{RSET} = 100 \text{ k}\Omega$	1.1	1.5	2.1	Α	
'SEI		$R_{RSET} = 49.9 \text{ k}\Omega$	1.1	1.4	1.6		
			$R_{RSET} = 200 \text{ k}\Omega$	1.1	1.8	2.4	Α
$I_{LIM}$	Current limit	$I_{VOUT}$ rising, $V_{VIN-VOUT} = 0.3 \text{ V}$ , pulsed test	$R_{RSET} = 100 \text{ k}\Omega$	2.3	3	3.7	Α
			$R_{RSET} = 49.9 \text{ k}\Omega$	4.6 5.5		6.3	Α
CT							
	Charge/discharge	I <sub>CT</sub> sourcing, V <sub>CT</sub> = 1 V, In current limit		29	35	41	μA
	current	$I_{CT}$ sinking (–2), $V_{CT}$ = 1 V, drive CT to 1 V, me	easure current	1	1.4	1.8	μΛ
	Threshold voltage	V <sub>CT</sub> rising				1.5	V
	Triicanola voltage	V <sub>CT</sub> falling, drive CT to 1 V, measure current		0.1	0.16	0.3	<b>V</b>
	ON/OFF fault duty cycle	V <sub>VOUT</sub> = 0 V	2.8%	3.7%	4.6%		
EN							
	Threshold voltage	V EN falling		0.8	1	1.5	V
	Tillesiloid voltage	Hysteresis		20	150	250	mV
	Input bias current	V <sub>EN</sub> = 2.4 V				0.5	^
	input bias current	$V_{\overline{EN}} = 0.2 \text{ V}$	-3.0	1	0.5	μΑ	
	Turn on propagation delay	$V_{VIN}$ = 3.3 V, $I_{LOAD}$ = 1 A, V $\overline{_{EN}}$ : 2.4 V $\rightarrow$ 0.2 V $V_{VOUT}$ : rising 90% × $V_{VIN}$	,		350	500	μs
	Turn off propagation delay	$V_{VIN}$ = 3.3 V, $I_{LOAD}$ = 1 A, V $\overline{\text{EN}}$ : 0.2 V $ ightarrow$ 2.4 V $V_{VOUT}$ : $\downarrow$ 10% × $V_{VIN}$	′,		30	50	μο



## **Electrical Characteristics (continued)**

Unless otherwise noted: 3 V  $\leq$  V<sub>VIN</sub>  $\leq$  18 V,  $\overline{EN}$  = 0 V,  $\overline{PG}$  =  $\overline{FLT}$  = open, R<sub>OUT</sub> = open, R<sub>RSET</sub> = 49.9 k $\Omega$ ,  $-40^{\circ}$ C  $\leq$  T<sub>J</sub>  $\leq$  125 $^{\circ}$ C, No external capacitor connected to VOUT

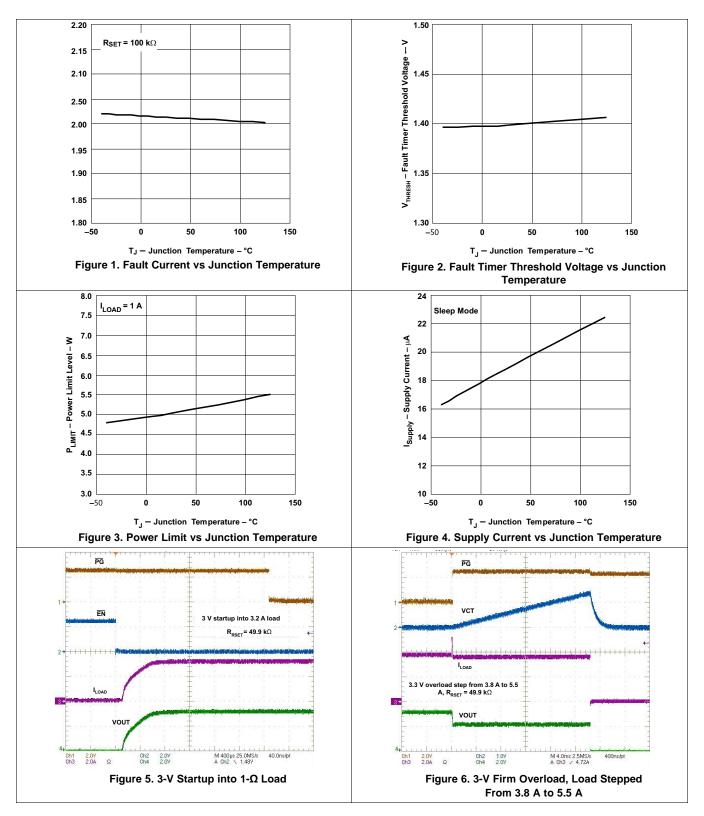
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
FLT			•			
V <sub>OL</sub>	Low level output voltage	$V_{CT} = 1.8 \text{ V}, I_{\overline{FLT}} = 1 \text{ mA}$		0.2	0.4	V
	Leakage current	V <sub>FLT</sub> = 18 V			1	μΑ
PG						
	PG threshold	V <sub>(VIN-VOUT)</sub> falling	0.4	0.5	0.75	
	PG threshold	Hysteresis	0.1	0.25	0.4	V
V <sub>OL</sub>	Low level output voltage	$I_{\overline{PG}} = 1 \text{ mA}$		0.2	0.4	v
	Leakage current	V <del>PG</del> = 18 V			1	μΑ
THER	MAL SHUTDOWN		•			
T <sub>SD</sub>	Thermal shutdown	Junction temperature rising		160		°C
		Hysteresis		10		

Submit Documentation Feedback

Copyright © 2009–2015, Texas Instruments Incorporated

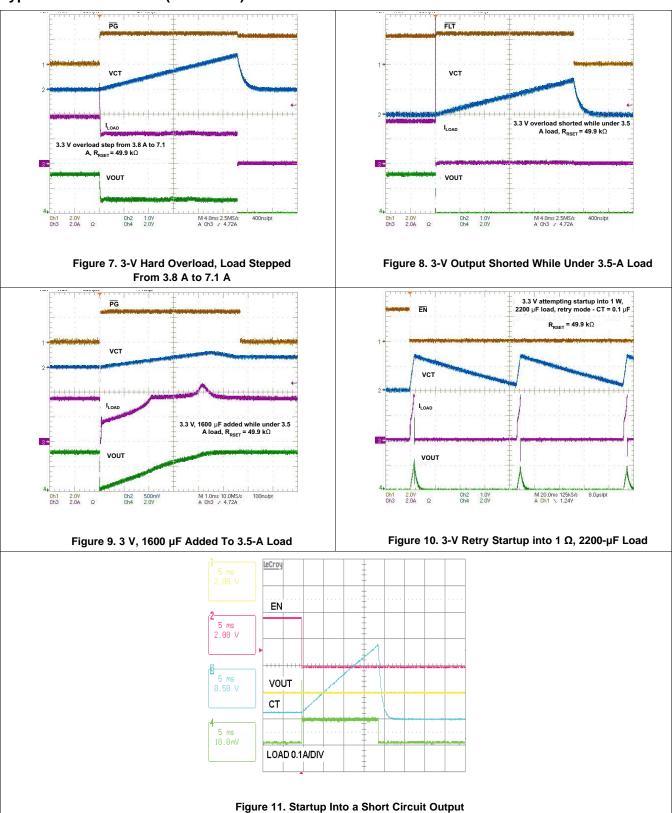


## 8.6 Typical Characteristics





## **Typical Characteristics (continued)**



Submit Documentation Feedback

Copyright © 2009–2015, Texas Instruments Incorporated



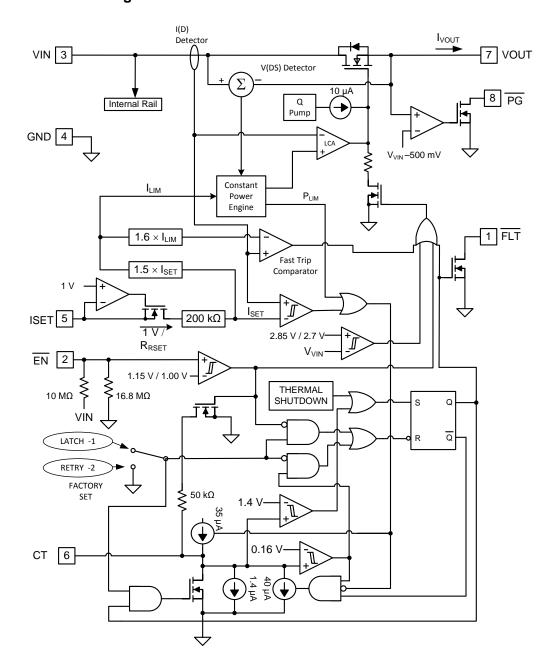
## 9 Detailed Description

## 9.1 Overview

The TPS2421 device provides highly integrated hot swap power management and superior protection in applications where the load is powered by busses up to 20 V.

The device has multiple programmable protection features. Load protection is accomplished by a non-current limiting fault threshold, a hard current limit, and a fault timer. Hotswap MOSFET protection is provided by power limit circuitry which protects the internal MOSFET against SOA related failures.

## 9.2 Functional Block Diagram



Copyright © 2009–2015, Texas Instruments Incorporated



## 9.3 Feature Description

#### 9.3.1 CT

Connect a capacitor from CT to GND to set the fault time. The fault timer starts when  $I_{VOUT}$  exceeds  $I_{SET}$  or when SOA protection mode is active, charging the capacitor with 35  $\mu$ A from GND towards an upper threshold of 1.4 V. If the capacitor reaches the upper threshold, the internal pass MOSFET is turned off. For the TPS2421-1 device, the MOSFET will remain off until  $\overline{EN}$  is cycled. For the TPS2421-2 device, the capacitor will discharge at 1.4  $\mu$ A to 0.16 V and then re-enable the pass MOSFET. If the upper threshold is not crossed, the capacitor will discharge at 40  $\mu$ A to 0.16 V and then to 0 V at 1.4  $\mu$ A. When the device is disabled, CT is pulled to GND through a 50-k $\Omega$  resistor.

The timer period must be chosen long enough to allow the external load capacitance to charge. The nominal (not including component tolerances) fault timer period is selected using Equation 1 where  $T_{FAULT}$  is the minimum timer period in seconds and  $C_{CT}$  is in Farads.

$$C_{CT} = \frac{T_{FAULT}}{40 \times 10^3} \tag{1}$$

For the TPS2421-2 device, the second and subsequent retry timer periods will be slightly shorter than the first retry period. CT nominal (not including component tolerances) discharge time,  $t_{SD}$  from 1.4 V to 0.16 V is shown in Equation 2, where  $C_{CT}$  is in Farads and  $t_{SD}$  is in seconds.

$$T_{SD} = 885.7 \times 10^3 \times C_{CT} \tag{2}$$

The nominal ratio of on to off times represents about a 3.7% duty cycle when a hard fault is present on the output.

#### 9.3.2 FLT

Open-drain output that pulls low on any condition that <u>causes</u> the output to open. These conditions are either an overload <u>with</u> a fault time-out, or a thermal shutdown.  $\overline{FLT}$  becomes operational before  $\underline{UV}$ , when  $V_{VIN}$  is greater than 1 V.  $\overline{FLT}$  will pulse low momentarily prior to the onset of  $V_{VOUT}$  ramp up during IN or  $\overline{EN}$  based start up.

#### 9.3.3 GND

This is the most negative voltage in the circuit and is used as reference for all voltage measurements unless otherwise specified.

#### 9.3.4 ISET

A resistor from this pin to GND sets both the fault current ( $I_{SET}$ ) and current limit ( $I_{LIM}$ ) levels. The current limit is internally set at 150% of the fault current. The fault timer described in the CT section starts when  $I_{VOUT}$  exceeds  $I_{SET}$ .

The internal MOSFET actively limits current if  $I_{VIN}$  reaches the current limit set point. The fault timer operation is the same in this mode as described previously.

The fault current value is programmed as shown in Equation 3:

$$R_{RSET} = \frac{200 \, k\Omega}{I_{SET}} \tag{3}$$

**EN:** When this pin is pulled low, the device is enabled. The input threshold is hysteretic, allowing the user to program a startup delay with an external RC circuit.  $\overline{\text{EN}}$  is pulled to VIN with a 10-M $\Omega$  resistor and to GND with a 16.8-M $\Omega$  resistor. Because high impedance pullup and pulldown resistors are used to reduce current draw, any external FET controlling this pin should be low leakage.

#### 9.3.5 VIN

Input voltage to the TPS2421 device. The recommended operating voltage range is 3 V to 20 V. Connect VIN to the power source.



## Feature Description (continued)

#### NOTE

(For TPS2421-1 only) Brownout-type conditions (VIN < 2.85 V) prior to start up can trigger the fault logic and prevent start up. For more information go to E2E.Tl.com.

#### 9.3.6 **VOUT**

Output connection for the TPS2421 device. V<sub>VOUT</sub> in the ON condition considering the ON resistance of the internal MOSFET, R<sub>ON</sub> is shown in Equation 4:

$$V_{VOUT} = V_{VIN} - R_{ON} \times I_{VOUT} \tag{4}$$

Connect VOUT to the load.

## 9.3.7 PG

Active low, Open Drain output, Power Good indicates that there is no fault condition and the output voltage is within 0.5 V of the input voltage. PG becomes operational before UV, whenever V<sub>VIN</sub> is greater than 1 V.

## 9.4 Device Functional Modes

## 9.4.1 Startup

Large inrush current occurs when power is applied to discharged capacitors and load. During the inrush period, the TPS2421 device operates in power limit (or SOA protect mode) managing the current as V<sub>VOUT</sub> rises. In SOA protect mode, the internal MOSFET power dissipation ([V<sub>VIN</sub> – V<sub>VOUT</sub>] x I<sub>VOUT</sub>) is regulated at 5W typical while the fault timer starts and C<sub>CT</sub> ramps up. As the charge builds on C<sub>LOAD</sub>, the current increases towards I<sub>LIM</sub>. When the capacitor is fully charged, I<sub>VOUT</sub> drops to the dc load value, the fault timer stops, and C<sub>CT</sub> ramps down. In order for the TPS2421 device to start properly, the fault timer duration must exceed C<sub>LOAD</sub> start up time, t<sub>ON</sub>. Start-up time without additional dc loading is calculated using Equation 5 where  $P_{LIM} = 5 \text{ W}$  (typical).

$$t_{ON} = \frac{C_{LOAD} \times P_{LIM}}{2 \times I_{LIM}^2} + \frac{C_{LOAD} \times V_{VIN}^2}{2 \times P_{LIM}}$$
(5)

When the load has a resistive component in addition to C<sub>LOAD</sub>, the fault time must be extended because the resistive load current is unavailable to charge C<sub>LOAD</sub>. Use Table 1 and Table 2 to predict start-up time in the presence of resistive dc loading.

Refer to the TPS2421 Design Calculator Tool (SLUC427) for assistance with design calculations.

Table 1. Start up Time (ms) with DC Loading:  $V_{IN} = 5 \text{ V}$ ,  $P_{LIM} = 3 \text{ W}$ ,  $I_{LIM} = 5 \text{ A}$ 

$R_{LOAD_{-}}(\Omega)$	C <sub>LOAD</sub> _ = 100 μF	C <sub>LOAD</sub> _ = 220 μF	C <sub>LOAD</sub> _ = 470 μF	C <sub>LOAD</sub> _ = 1000 μF
1000	0.43	0.95	2.03	4.33
10	0.5	1.11	2.36	5.03
5	0.61	1.34	2.87	6.1
3	0.91	2	4.28	9.11
2.5	1.31	2.88	6.14	13.07

Table 2. Start up Time (ms) with DC Loading:  $V_{IN} = 12 \text{ V}$ ,  $P_{LIM} = 3W$ ,  $I_{LIM} = 5 \text{ A}$ 

$R_{LOAD_{-}}(\Omega)$	C <sub>LOAD</sub> = 100 μF	C <sub>LOAD</sub> _ = 220 μF	C <sub>LOAD</sub> _ = 470 μF	C <sub>LOAD</sub> _ = 1000 μF
10000	2.46	5.41	11.56	24.59
100	2.67	5.87	12.55	26.69
50	2.93	6.45	13.79	29.34
15	6.7	14.74	31.5	67.01
13	11.68	25.69	54.87	116.75

Copyright © 2009-2015, Texas Instruments Incorporated



#### 9.4.2 Maximum Allowable Load to Ensure Successful Start up

The power limiting function of the TPS2421 device provides very effective protection for the internal FET. As expected, there is a supply voltage dependent maximum allowable load required for successful startup. Loads above this can cause the output to shut off due to CT timeout or thermal shutdown because  $V_{VOUT}$  hangs at an intermediate voltage below  $V_{IN}$ . The equation for maximum load (or  $R_{MIN}$  is derived using the circuit equations for  $V_{VOUT}$  as a function of  $V_{VIN}$ ,  $R_{LOAD}$ ,  $P_{LIM}$ , and the result is quadratic in form.

$$R_{MIN} \times I^2 - V_{VIN} \times I + P_{LIM\_MIN} = 0$$
(6)

$$I = \frac{V_{VIN} \pm \sqrt{V_{VIN}^2 - 4 \times R_{MIN} \times P_{LIM\_MIN}}}{2 \times R_{MIN}}$$
(7)

$$R_{MIN} \times I = V_{VOUT} = \frac{V_{VIN} \pm \sqrt{V_{VIN}^2 - 4 \times R_{MIN} \times P_{LIM\_MIN}}}{2}$$
(8)

When  $R_{LOAD} < R_{MIN}$ , the numerical result for  $V_{VOUT}$  is real ( $V_{VIN}^2 - 4 \times R_{LOAD} \times P_{LIM} > 0$ ) and less than  $V_{VIN}$  meaning the circuit will not start (CT or thermal shutdown). When  $R_{LOAD} > R_{MIN}$ , the numerical result for  $V_{VOUT}$  is imaginary ( $V_{VIN}^2 - 4 \times R_{LOAD} \times P_{LIM} < 0$ ) and the circuit will start ( $V_{VOUT} = V_{VIN}$ ). Ensure that  $R_{LOAD}$  is  $V_{MIN}$  per Equation 10.

$$4 \times R_{MIN} \times P_{LIM\_MIN} > V_{VIN}^2 \tag{9}$$

$$R_{LOAD} > R_{MIN} = \frac{V_{VIN}^2}{4 \times P_{LIM\_MIN}} = \frac{V_{VIN}^2}{12}$$
(10)

#### 9.4.2.1 Enable Pin Considerations

For the case when  $\overline{\text{EN}}$  is simply connected to GND, the TPS2421 device starts ramping the voltage on VOUT as VIN rises above UVLO (approximately 2.85 V typical). If IN does not ramp monotonically, the TPS2421 may momentarily turn off then on during startup if IN falls below approximately 2.7 V. To avoid this problem,  $\overline{\text{EN}}$  assertion can be delayed until IN is sufficiently above UVLO. A simple approach is shown in Figure 12. The 100-k $\Omega$  pullup resistor will de-assert  $\overline{\text{EN}}$  when VIN is above approximately 1.75 V maximum which is well below the minimum UVLO of approximately 2.6 V. The Zener diode ensures that  $\overline{\text{EN}}$  remains below 5V. User control to enable the TPS2421 device is applied at the ON node to turn on the FET once IN has risen sufficiently above UVLO.

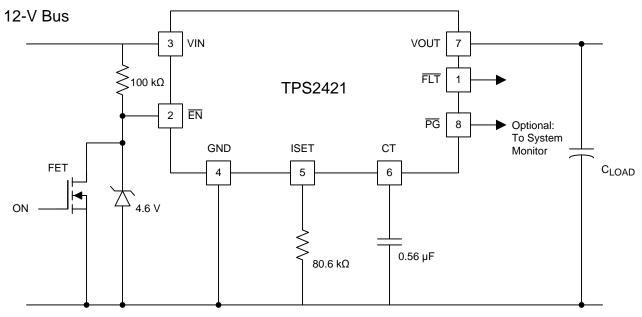


Figure 12. EN Delay Circuit



#### 9.4.2.2 Fault Timer

The fault timer is active when the TPS2421 device is in SOA protect mode or the current is above  $I_{SET}$ . Figure 13 illustrates operation during non-faulted start up ( $C_{LOAD} = 470~\mu F$  and  $I_{VOUT} = 1~A$  in a 12 V system).  $C_{CT}$  charges at approximately 35  $\mu A$  until TPS2421 device exits SOA protect mode, discharges quickly (approximately 40  $\mu A$ ) to approximately 0.16 V, and then decays slowly (approximately 1.4  $\mu A$ ) towards zero.

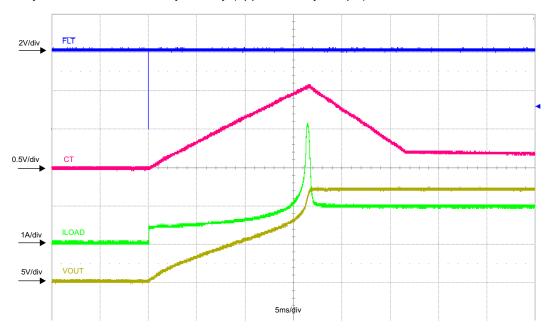


Figure 13. Fault Timer Operation During Startup

 $C_{\text{CT}}$  can be chosen for fault-free start up including expected  $C_{\text{LOAD}}$  and  $C_{\text{CT}}$  capacitance tolerance as shown in Equation 11.

$$C_{CT} = \frac{(1 + C_{LOAD\_TOL} + C_{CT\_TOL}) \times t_{ON}}{40000}$$
(11)

## 9.4.2.3 Normal Operation

When load current exceeds  $I_{SET}$  during normal operation the fault timer starts. If load current drops below  $I_{SET}$  before the fault timer expires, normal operation continues. If load current stays above the  $I_{SET}$  threshold the fault timer expires and a fault is declared. When a fault is declared a TPS2421-1 device turns off an can be restarted by cycling power or toggling the  $\overline{EN}$  signal. A TPS2421-2 device attempts to turn on at a 3.7% duty cycle until the fault is cleared. When  $I_{LIM}$  is reached during a fault the device goes into current limit and the fault timer keeps running.

#### 9.4.2.4 Start up into a Short

The controller attempts to power on into a short for the duration of the timer. Figure 11 shows a small current resulting from power limiting the internal MOSFET. This occurs only once for the TPS2421-1 device. For the TPS2421-2 device, the cycle repeats at a 3.7% duty cycle as shown in Figure 10.

#### 9.4.3 Shutdown Modes

#### 9.4.3.1 Hard Overload - Fast Trip

When a hard overload causes the load current to exceed approximately 1.6 x I<sub>LIM</sub> the TPS2421 immediately shuts off current to the load without waiting for the fault timer to expire. After such a shutoff the TPS2421 device enters startup mode and attempts to apply power to the load. If the hard overload was caused by a transient, then normal startup can be expected. If the hard overload is caused by a persistent, continuous failure then the TPS2421 device enters into current limit during the restart attempt and either latches off (TPS2421-1) or attempts retry (TPS2421-2).

Copyright © 2009–2015, Texas Instruments Incorporated



#### 9.4.3.2 Overcurrent Shutdown

Overcurrent shutdown occurs when the output current exceeds  $I_{SET}$  for the duration of the fault timer. Figure 18 shows a step rise in output current which exceeds the  $I_{SET}$  threshold but not the  $I_{LIM}$  threshold. The increased current is on for the duration of the timer. When the timer expires, the output is turned off.

#### 9.5 Programming

## 9.5.1 Fault (I<sub>SET</sub>) and Current-limit (I<sub>LIM</sub>) Thresholds

The  $I_{SET}$  and  $I_{LIM}$  thresholds is user programmable with a single external resistor connected to ISET and the  $I_{LIM}$  threshold is internally set according to the  $I_{LIM}/I_{SET}$  ratio specified in the electrical characteristics table. The TPS2421 device uses an internal regulation loop to provide a regulated voltage on the ISET pin. The fault and current-limit thresholds are proportional to the current sourced out of ISET. The recommended 1% resistor range is 49.9 k $\Omega \le R_{RSET} \le 200$  k $\Omega$  to ensure the rated accuracy. Many applications require that minimum fault and current limits are known or that maximum current limit is bounded. Considering the tolerance of the fault and current limit thresholds, as well as  $R_{RSET}$  when selecting values is important. See the *Electrical Characteristics* table for specific fault and current limit settings.

Using the data for  $I_{SET}$  and  $I_{LIM}$  from the *Electrical Characteristics*, equations are generated and used for other set points. Equation 12 and Equation 13 are used to calculate minimum and maximum  $I_{SET}$  where  $R_{RSET,max}$  and  $R_{RSET,min}$  include  $R_{RSET,min}$  tolerances. Equation 14 and Equation 15 calculate  $R_{RSET,max}$  and  $R_{RSET,min}$  where  $R_{TOL}$  is the 1% resistor tolerance.

$$I_{SET,min} = \frac{185.58}{R_{RSET,max}} - 0.13 \tag{12}$$

$$I_{SET,max} = \frac{213.68}{R_{RSET,min}} + 0.13 \tag{13}$$

$$R_{RSET,min} = (1 + R_{TOL}) \times \frac{213.68}{I_{SET,max} - 0.13}$$
 (14)

$$R_{RSET,max} = (1 - R_{TOL}) \times \frac{185.58}{I_{SET,min} + 0.13}$$
(15)

Equation 16 and Equation 17 are used to calculate minimum and maximum  $I_{LIM}$  where  $R_{RSET,max}$  and  $R_{RSET,min}$  include  $R_{RSET}$  tolerances.

$$I_{LIM,min} = \frac{232.19}{R_{RSET,max}} - 0.06 \tag{16}$$

$$I_{LIM,max} = \frac{259.26}{R_{RSET,min}} + 1.11 \tag{17}$$



# 10 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 10.1 Application Information

## 10.2 Typical Application

The TPS2421 is an integrated FET hot swap device. It is typically used for Hot-Swap and Power rail protection applications. It operates from 3 V to 20 V with programmable fault current limit, and fault Timer.

The following design procedure can be used to select component values for the device. This section presents a simplified discussion of the design process.

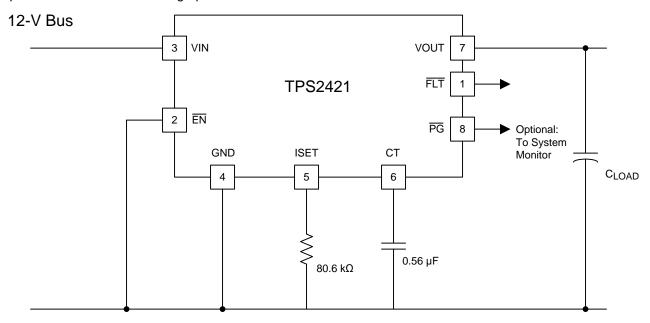


Figure 14. Design Example Schematic

#### 10.2.1 Design Requirements

A typical design is shown in Figure 14 with the following requirements:

- Nominal input voltage, V<sub>VIN</sub>: 12 V
- Maximum expected load current, I<sub>VOUT</sub>: 2.1 A
- Load capacitance, C<sub>LOAD</sub>: 220 μF
- Expected resistive load, R<sub>LOAD</sub> during start up: 15 Ω
- Example calculations are shown in the TPS2421 Design Calculator Tool (SLUC427).



## **Typical Application (continued)**

#### 10.2.2 Detailed Design Procedure

 Calculate maximum R<sub>RSET</sub> to ensure that minimum I<sub>SET</sub> is above maximum operating load current using Equation 15 as shown below in Equation 18.

$$R_{RSET,max} = 0.99 \times \frac{185.58}{2.1 + 0.13} = 82.39 \text{k}\Omega$$
(18)

- Choose a standard 1% value below  $R_{RSET,max}$  for  $R_{RSET} = 80.6k\Omega$
- $I_{SET,min}$  = 2.15 A using Equation 12 and will meet the maximum operating current requirement of 2.1 A without starting the fault timer during maximum steady state operation for  $R_{RSET}$  = 80.6 k $\Omega$ , 1%.
- $I_{SET.max} = 4.359$  A using Equation 13 for  $R_{RSET} = 80.6 \Omega$ , 1%.
- 2. Calculate minimum and maximum IIIM.
  - $I_{LIM,min}$  = 2.792A and  $I_{LIM,max}$  = 4.359 A using Equation 16 and Equation 17 for  $R_{RSET}$  = 80.6 k $\Omega$ , 1%.
- 3. Minimum  $R_{LOAD}$  at start up using Equation 10 is 12  $\Omega$ . Because  $R_{LOAD}$  = 15  $\Omega$  is present during circuit start up, use  $t_{ON}$  = 15ms from Table 2 for  $C_{LOAD}$  = 220  $\mu$ F and  $R_{LOAD}$  = 15  $\Omega$ .
  - Calculate C<sub>CT</sub> = 0.48 μF including C<sub>LOAD</sub> and C<sub>CT</sub> tolerances (C<sub>LOAD\_TOL</sub> = 20% and C<sub>CT\_TOL</sub> = 10%) using Equation 19.

$$C_{CT} = \frac{(1 + C_{LOAD\_TOL} + C_{T\_TOL}) \times t_{ON}}{40000} = \frac{(1 + 0.2 + 0.1) \times 0.012}{40000} = 0.48 \ \mu F$$
(19)

#### 10.2.2.1 Transient Protection

The need for transient protection in conjunction with hot-swap controllers should always be considered. When the TPS2421 device interrupts current flow, input inductance generates a positive voltage spike on the input and output inductance generates a negative voltage spike on the output. Such transients can easily exceed twice the supply voltage if steps are not taken to address the issue. Typical methods for addressing transients include;

- · Minimizing lead length/inductance into and out of the device
- Voltage Suppressors (TVS) on the input to absorb inductive spikes
- Schottky diode across the output to absorb negative spikes
- · A combination of ceramic and electrolytic capacitors on the input and output to absorb energy
- Use PCB GND planes

The following equation estimates the magnitude of these voltage spikes:

$$V_{SPIKE(absolute)} = V_{NOM} + I_{LOAD} \times \sqrt{\frac{L}{C}}$$

#### where

- V<sub>NOM</sub> is the nominal supply voltage
- I<sub>LOAD</sub> is the load current
- · C is the capacitance present at the input or output of the TPS2421 device
- L equals the effective inductance seen looking into the source or the load

  (20)

Calculating the inductance due to a straight length of wire is shown in Equation 21.

$$L_{straightwire} \approx 0.2 \times L \times V_{VIN} \left( \frac{4 \times L}{D} - 0.75 \right) \left( nH \right)$$

where

. L is the length of the wire

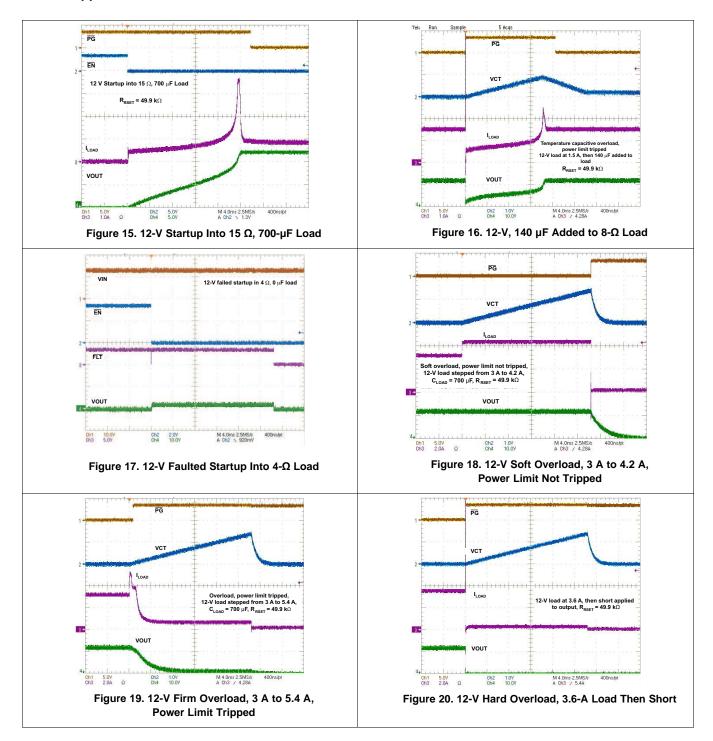
D is diameter of the wire



# **Typical Application (continued)**

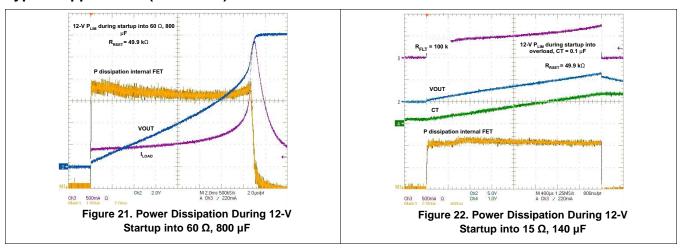
Some applications may require the addition of a TVS to prevent transients from exceeding the absolute ratings if sufficient capacitance cannot be included.

## 10.2.3 Application Curves





## **Typical Application (continued)**



## 11 Power Supply Recommendations

## 11.1 PowerPad™

When properly mounted the PowerPad package provides significantly greater cooling ability than an ordinary package. To operate at rated power the PowerPAD must be soldered directly to the PC board GND plane directly under the device. The PowerPAD is at GND potential and can be connected using multiple vias to inner layer GND. Other planes, such a the bottom side of the circuit board can be used to increase heat sinking in higher current applications. Refer to Technical Briefs: *PowerPad™ Thermally Enhanced Package* (SLMA002) and *PowerPad™ Made Easy* (SLMA004) or more information on using this PowerPad™ package. These documents are available at www.ti.com (Search by Keyword).



## 12 Layout

## 12.1 Layout Guidelines

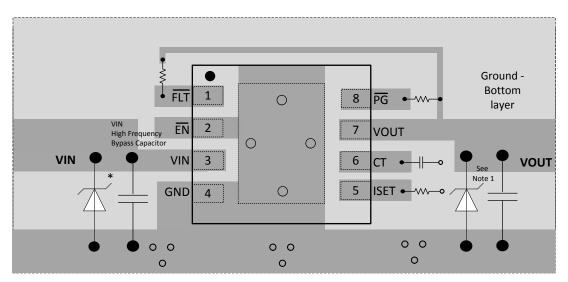
- Locate all TPS2421 support components, R<sub>RSET</sub>, C<sub>CT</sub>, or any input or output voltage clamps, close to their connection pin.
- Connect the other end of the component to the inner layer GND without trace length.
- The trace routing the R<sub>RSET</sub> resistor to the TPS2421 device must be as short as possible to reduce parasitic
  effects on fault and current-limit accuracy.

## 12.2 Layout Example

Top layer

Bottom layer signal ground plane

O Via to signal ground plane



(1) Optional: Needed only to suppress the transients caused by inductive load switching.

Figure 23. Layout



## 13 Device and Documentation Support

#### 13.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 3. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY	
TPS2421-1	Click here	Click here	Click here	Click here	Click here	
TPS2421-2	Click here	Click here	Click here	Click here	Click here	

## 13.2 Trademarks

PowerPad is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

## 13.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 13.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

# 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





5-Dec-2014

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	_		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPS2421-1DDA	ACTIVE	SO PowerPAD	DDA	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	2421-1	Samples
TPS2421-1DDAR	ACTIVE	SO PowerPAD	DDA	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	2421-1	Samples
TPS2421-2DDA	ACTIVE	SO PowerPAD	DDA	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	2421-2	Samples
TPS2421-2DDAR	ACTIVE	SO PowerPAD	DDA	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU   CU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	2421-2	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.



# PACKAGE OPTION ADDENDUM

5-Dec-2014

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2014

## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2421-1DDAR	SO Power PAD	DDA	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
TPS2421-2DDAR	SO Power PAD	DDA	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 5-Dec-2014



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2421-1DDAR	SO PowerPAD	DDA	8	2500	364.0	364.0	27.0
TPS2421-2DDAR	SO PowerPAD	DDA	8	2500	364.0	364.0	27.0

# DDA (R-PDSO-G8)

# PowerPAD ™ PLASTIC SMALL-OUTLINE



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">http://www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. This package complies to JEDEC MS-012 variation BA

PowerPAD is a trademark of Texas Instruments.



# DDA (R-PDSO-G8)

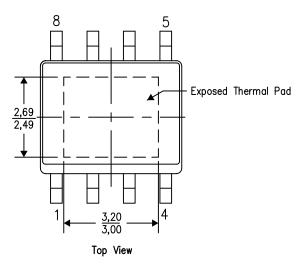
# PowerPAD™ PLASTIC SMALL OUTLINE

## THERMAL INFORMATION

This PowerPAD package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206322-7/L 05/12

NOTE: A. All linear dimensions are in millimeters



#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

#### Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive **Amplifiers** amplifier.ti.com Communications and Telecom www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps DSP dsp.ti.com **Energy and Lighting** www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical Logic Security www.ti.com/security logic.ti.com

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers microcontroller.ti.com Video and Imaging www.ti.com/video

RFID www.ti-rfid.com

OMAP Applications Processors www.ti.com/omap TI E2E Community e2e.ti.com

Wireless Connectivity www.ti.com/wirelessconnectivity